

ALTERNATIVE TO PTO/SB/08A/B
(Based on PTO 08-08 version)

Substitute for form 1449/PTO INFORMATION DISCLOSURE STATEMENT BY APPLICANT <i>(Use as many sheets as necessary)</i>				Complete if Known	
				Application Number	10/514,429
				Filing Date	July 12, 2005
				First Named Inventor	Robert DWILINSKI
				Art Unit	2881
				Examiner Name	M. J. Logie
Sheet	1	of	3	Attorney Docket Number	204552033800

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Examiner Initials*	Cite No. ¹	Document Number	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
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/Michael Logie/

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ALL REFERENCES CONSIDERED EXCEPT WHERE LINED THROUGH. /M.L./

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				Art Unit	2881
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NON PATENT LITERATURE DOCUMENTS					
Examiner Initials*	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.			T ²
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	52.	Japanese Notification of Reason(s) for Refusal, mailed December 16, 2008, directed to Japanese Patent Application No. 2004-505416; 7 pages			✓
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/Michael Logie/

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Examiner Signature	/Michael Logie/	Date Considered	04/28/2009
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